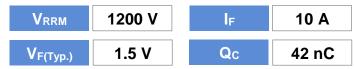


### Silicon Carbide Schottky Barrier Diode



#### Features

- Temperature Independent Switching Behavior
- High Surge Current Capability
- Positive Temperature Coefficient on VF
- Low Conduction Loss
- Zero Reverse Recovery
- High junction temperature 175 °C
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

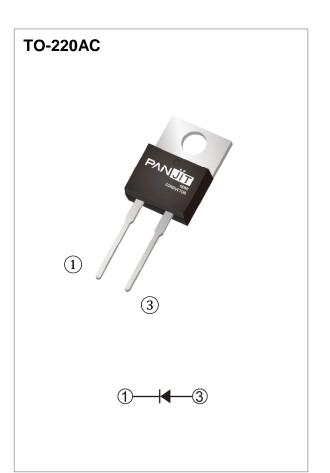
- Case: TO-220AC molded plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.067 ounces, 1.89 grams

### Application

• PFC, UPS, PV Inverter, EV Charging Station, Welder

### Maximum Ratings and Thermal Characteristics (Tc = 25 °C unless otherwise specified)

PARAMETE	SYMBOL	LIMIT	UNITS		
Repetitive Peak Reverse Voltage	Vrrm	1200	V		
DC Blocking Voltage	VDC	1200	V		
Continuous Forward Current	Tc= 155 °C	IF	10	А	
Repetitive Peak Surge Current	$T_{C}=25 \circ C$ , $t_{p}=10ms$		48		
Half Sine Wave, D=0.1	$T_C=125 \ ^{\circ}C$ , $t_p =10ms$	IFRM	40	A	
Peak Forward Surge Current	$T_{C}=25 \text{ °C}$ , $t_{p}=10 \text{ms}$		76	A	
Half Sine Wave	$T_C=125 \circ C$ , $t_p = 10ms$		68		
Peak Forward Surge Current $t_p = 10us$ , Pulse	IFSM	640	А		
Maximum Power Dissipation	P <sub>total</sub>	151.5	W		
Operating Junction Temperature Ra	TJ	-55~175	°C		
Storage Temperature Range	Tstg	-55~175	°C		





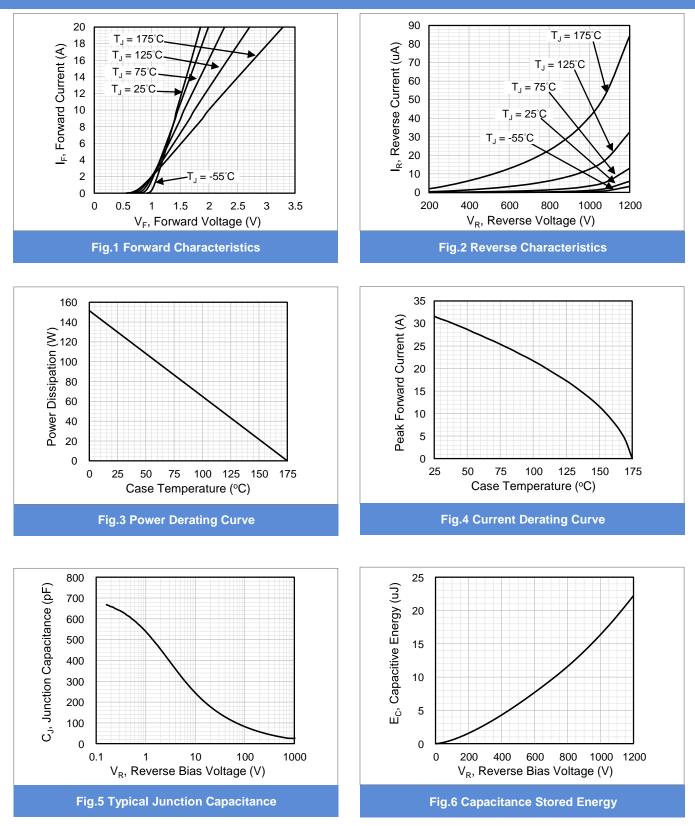
# **Electrical Characteristics** ( $T_c = 25$ °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Forward Voltage Drop	VF	I <sub>F</sub> = 10 A, T <sub>J</sub> = 25 °C	-	1.5	1.7	V	
		I <sub>F</sub> = 10 A, T <sub>J</sub> = 175 °C	-	2.0	-		
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 1200 V, T <sub>J</sub> = 25 °C	-	6	100	μA	
		V <sub>R</sub> = 1200 V, T <sub>J</sub> = 175 °C	-	0.085	-	mA	
Total Capacitive Charge	Qc	I <sub>F</sub> = 10 A, V <sub>R</sub> = 800V	-	42	-	nC	
Total Capacitance	С	$V_R = 1V$ , f = 1MHz	-	529	-	pF	
		V <sub>R</sub> = 400V, f = 1MHz	-	36	-	pF	
		V <sub>R</sub> = 800V, f = 1MHz	-	25	-	pF	
Capacitance Stored Energy	Ec	V <sub>R</sub> = 800V	-	12	-	μJ	
Thermal Resistance	Rejc		-	0.99	-	°C/W	



# PCDP10120G1



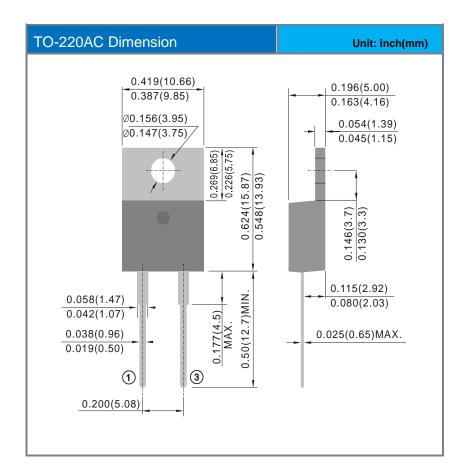




### **Product and Packing Information**

Part No. Package Type		Packing Type	Marking	
PCDP10120G1	TO-220AC	50pcs / Tube	CDP10120G1	

### **Packaging Information**





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